



**COLLEGE OF ENGINEERING  
PUTRAJAYA CAMPUS  
FINAL EXAMINATION**

**SEMESTER 1 2019 / 2020**

PROGRAMME : **Bachelor of Electrical & Electronics Engineering (Honours)  
Bachelor of Electrical Power Engineering (Honours)**

SUBJECT CODE : **EEEB273/EEEB2014**

SUBJECT : **ELECTRONIC ANALYSIS AND DESIGN II**

DATE : **September 2019**

DURATION : **3 hours**

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**INSTRUCTIONS TO CANDIDATES:**

1. This paper contains **FIVE (5)** questions in **TEN (10)** pages.
2. Answer **ALL** questions.
3. Write **all** answers in the answer booklet provided. Use **pen** to write your answer.
4. Write answer to different question on a **new page**.

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***THIS QUESTION PAPER CONSISTS OF TEN (10) PRINTED PAGES INCLUDING THIS COVER PAGE.***

**Question 1 [20 marks]**

As a graduate IC design engineer, you are given a task to design a circuit that meet these specifications:

- BJT current source that utilizes **3 npn transistors** such that the output current ( $I_O$ ) = **0.25 mA**
- The circuit output current ( $I_O$ ) must be **least affected** by change in output voltage ( $V_O$ )
- Transistor parameters are:  $\beta = 60$ ,  $V_A = 100$  V, and  $V_{BE(on)} = 0.7$  V
- The power supplies:  $V^+ = 5$  V,  $V^- = -5$

(a) Name and draw the specified circuit with clear details of the  $Q_1$ ,  $Q_2$  placements, currents and voltages involved. **[5 marks]**

(b) Assume all transistors are matched, derive the relationship between output current ( $I_O$ ) and the reference current ( $I_{REF}$ ). **[5 marks]**

(c) Based on your drawing in part (a), **design** the circuit such that it meets the specification. **[4 marks]**

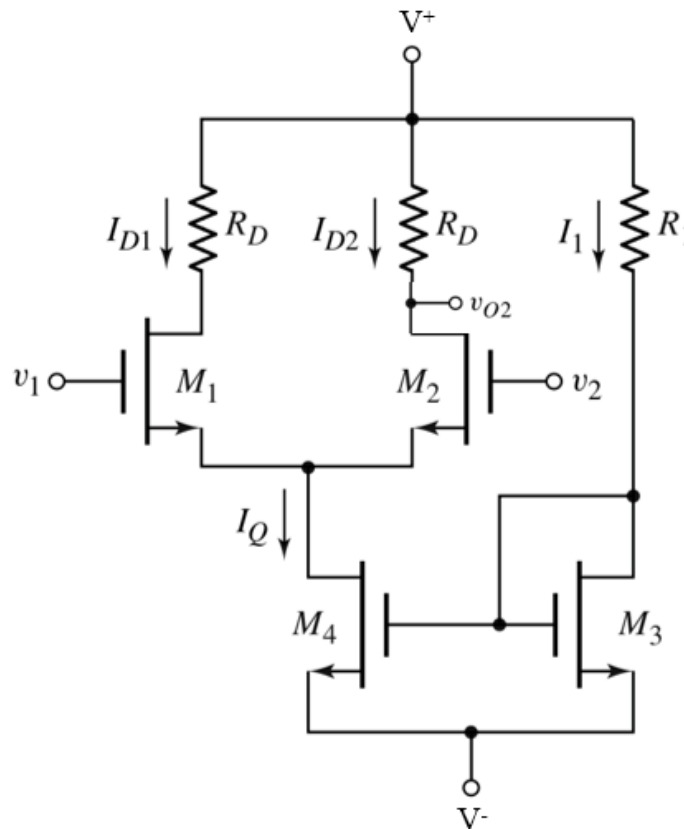
(d) What is the change in output current ( $I_O$ ) as the output voltage changes from **1V to 5V**. **[6 marks]**

**Question 2 [20 marks]**

(a) Consider a MOSFET differential amplifier circuit with power supply  $V^+ = 5\text{ V}$ ,  $V^- = 0\text{ V}$  as shown in **Figure 1**. Consider transistor parameters where  $k' = 100\ \mu\text{A}/\text{V}^2$  and  $V_{TN} = 0.3\text{ V}$  for all transistors. It is given that current  $I_{D1} = 150\ \mu\text{A}$  and width-to-length ratio of transistor  $M_1$ ,  $\left(\frac{w}{L}\right)_1 = 2$ . The differential output voltage is taken at the drain of transistor  $M_2$  with respect to the ground.

(i) Determine the value of  $R_D$  such that  $v_{O2}$  is biased at  $3.5\text{ V}$ . [2 marks]

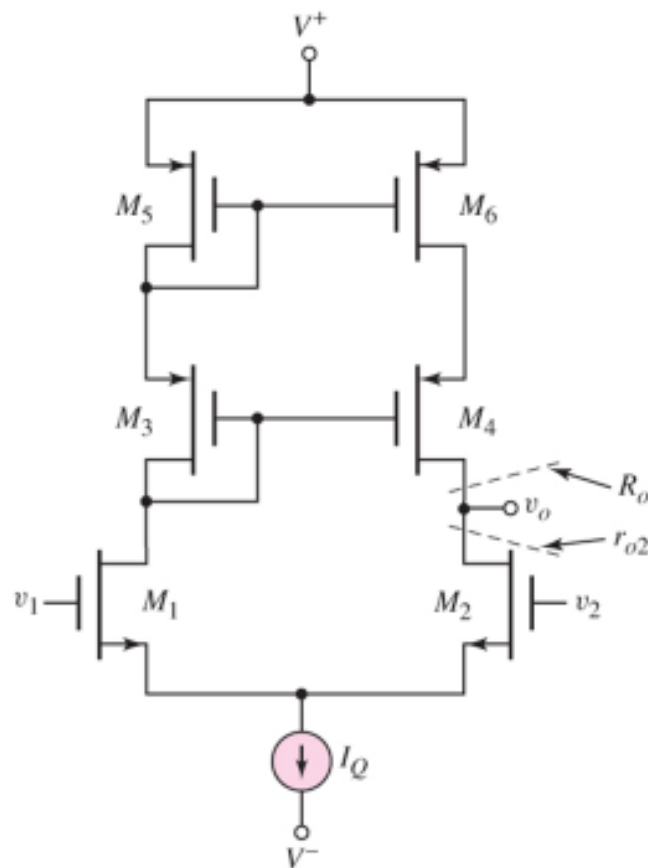
(ii) Calculate the differential gain of the amplifier. [3 marks]



**Figure 1**

(b) Consider a MOSFET differential amplifier with active load shown in **Figure 2**, with power supply  $V^+ = 10\text{ V}$  and  $V^- = -10\text{ V}$ . Transistor parameters are:  $V_{TP} = -0.5\text{ V}$ ,  $V_{TN} = 0.4\text{ V}$ ,  $k_n' = 80\mu\text{A/V}^2$ ,  $k_p' = 25\mu\text{A/V}^2$ ,  $\lambda_n = 0.015\text{ V}^{-1}$  and  $\lambda_p = 0.03\text{ V}^{-1}$ .

The constant current source is implemented using a **cascode** current source. **Design** the differential amplifier with active load circuit such that **output voltage range is 80% of the power supply voltage**, and the **maximum power dissipation is 1mW**. Ignore the power dissipation in the biasing circuitry. State all your assumptions. **[15 marks]**



**Figure 2**

**Question 3 [15 marks]**

A simple bipolar op-amp is shown in **Figure 3**. Study **Figure 3** carefully.

**Neglect base currents.** Assume that parameters for all transistors are  $V_{BE(on)} = 0.7 \text{ V}$ ,  $\beta = 200$ , and  $V_A = \infty$ . **Bias current** for the differential amplifier is  $I_Q = 1.4 \text{ mA}$ .

- (a) What is the **name** of the amplifiers or circuits with transistors and resistors used in the **Gain Stage** and the **Output Stage**? Indicate the transistors and resistors used in each circuit.

[5 marks]

- (b) With small-signal analysis, values of gain  $A_{d1}$  for the differential amplifier,  $r_{\pi 3}$ , and gain  $A_{v2}$  for the Gain Stage can be found using the following **Equations (3.1) to (3.3)**.

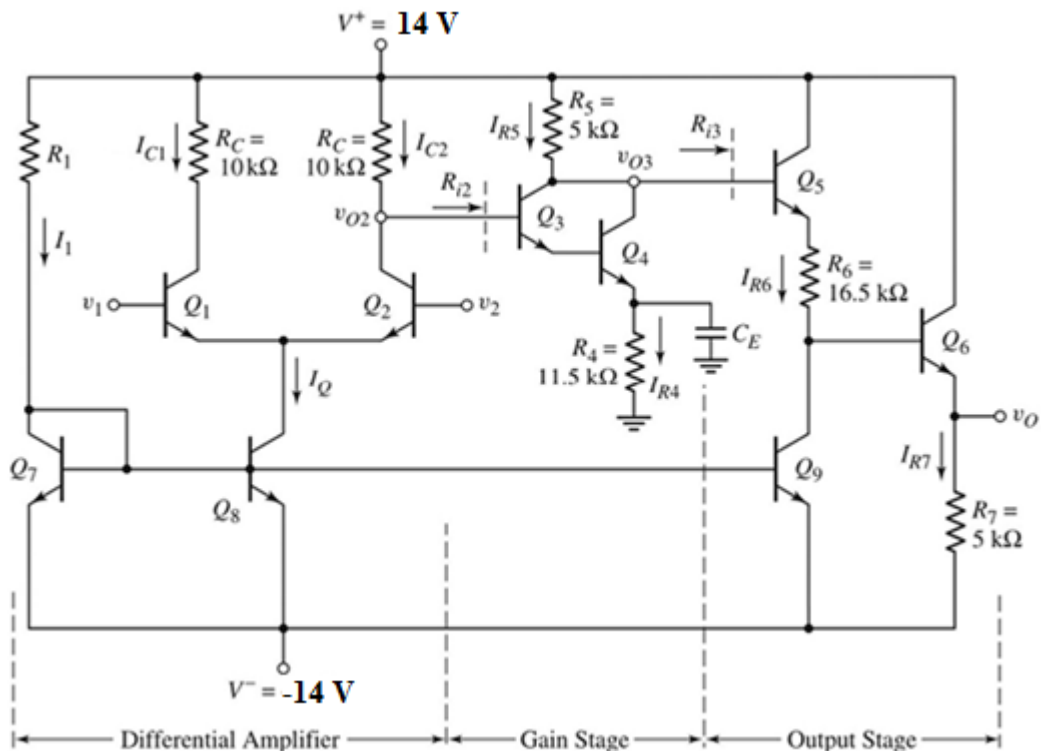
$$A_{d1} = \frac{v_{O2}}{v_d} = \frac{g_{m2}}{2} (R_C || R_{i2}) \quad (3.1)$$

$$r_{\pi 3} \cong \beta r_{\pi 4} \quad (3.2)$$

$$A_{v2} \cong \frac{I_{R4}}{2V_T} (R_5) \quad (3.3)$$

Calculate the **total overall small-signal voltage gain ( $A_d$ )** for the bipolar op-amp.

[10 marks]



**Figure 3**

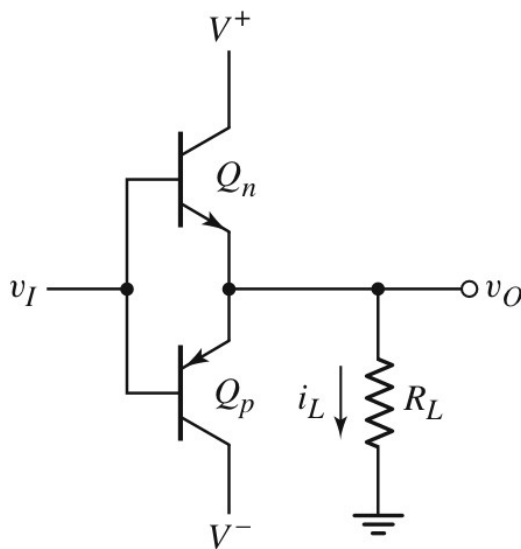
**Question 4 [25 marks]**

(a) Refer to **Figure 4** below for a **Class B** output stage implemented using the push-pull configuration of  $Q_n$  and  $Q_p$  transistors. Let  $V_{BE(on)} = V_{EB(on)} = 0.6V$ . Sketch the **voltage transfer characteristic** ( $v_o$  vs  $v_i$ ) for the class B output stage. Clearly indicate the conducting and non-conducting transistors in the relevant zones. **[5 marks]**

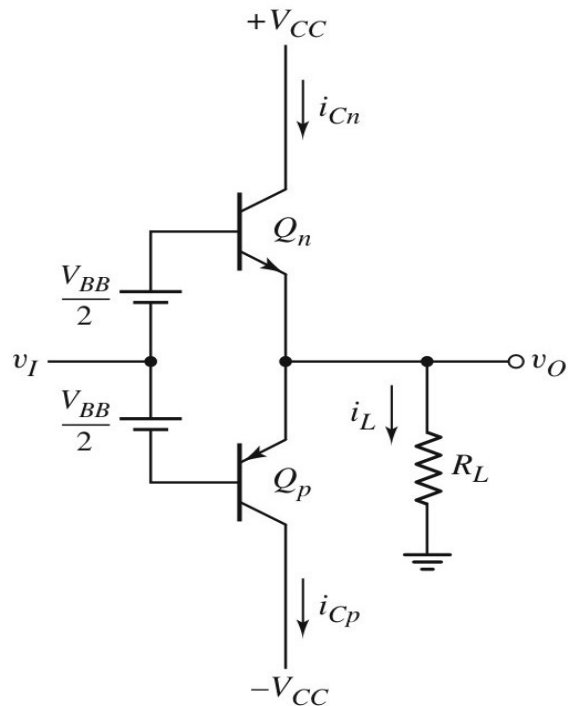
(b) For the **class AB** output stage given in **Figure 5**, parameters are  $V_{CC} = 10V$ ,  $R_L = 100\Omega$ . For the transistors,  $I_s = 5 \times 10^{-15}A$ ,  $\beta = \infty$ .

(i) For the **quiescent condition** when  $v_I = 0$ , it is given that  $V_{BE_n} = V_{EB_p} = 0.7V$ . Calculate the **DC collector currents** of  $Q_n$  and  $Q_p$ . **[4 marks]**

(ii) For an output voltage of  $v_o = -3V$ , calculate load current  $i_L$ , transistor currents  $i_{C_n}$  and  $i_{C_p}$ . **[6 marks]**



**Figure 4**



**Figure 5**

(c) Refer to the MC14573 opamp of **Figure 6**. It is given that for the circuit,  $V^+ = 10\text{V}$  and  $V^- = -10\text{V}$ . For all transistors,  $|V_T| = 0.8\text{V}$ ,  $k_n' = 40\mu\text{A}/\text{V}^2$ ,  $k_p' = 20\mu\text{A}/\text{V}^2$ ,  $\lambda_n = 0.01\text{V}^{-1}$ ,  $\lambda_p = 0.02\text{V}^{-1}$ . Also  $\left(\frac{w}{L}\right)_{3,4} = 10$  and for other transistors (except for the biasing circuitry),  $\left(\frac{w}{L}\right)_{\text{others}} = 20$ .

Design the biasing circuit such that  $I_Q = I_{D8} = 2\text{mA}$  when  $\left(\frac{w}{L}\right)_6 = 4\left(\frac{w}{L}\right)_5$ . The **minimum voltage** for current source  $V_{I_Q}$  is **1V**. What is the **maximum common mode input voltage** for the circuit? **[10 marks]**

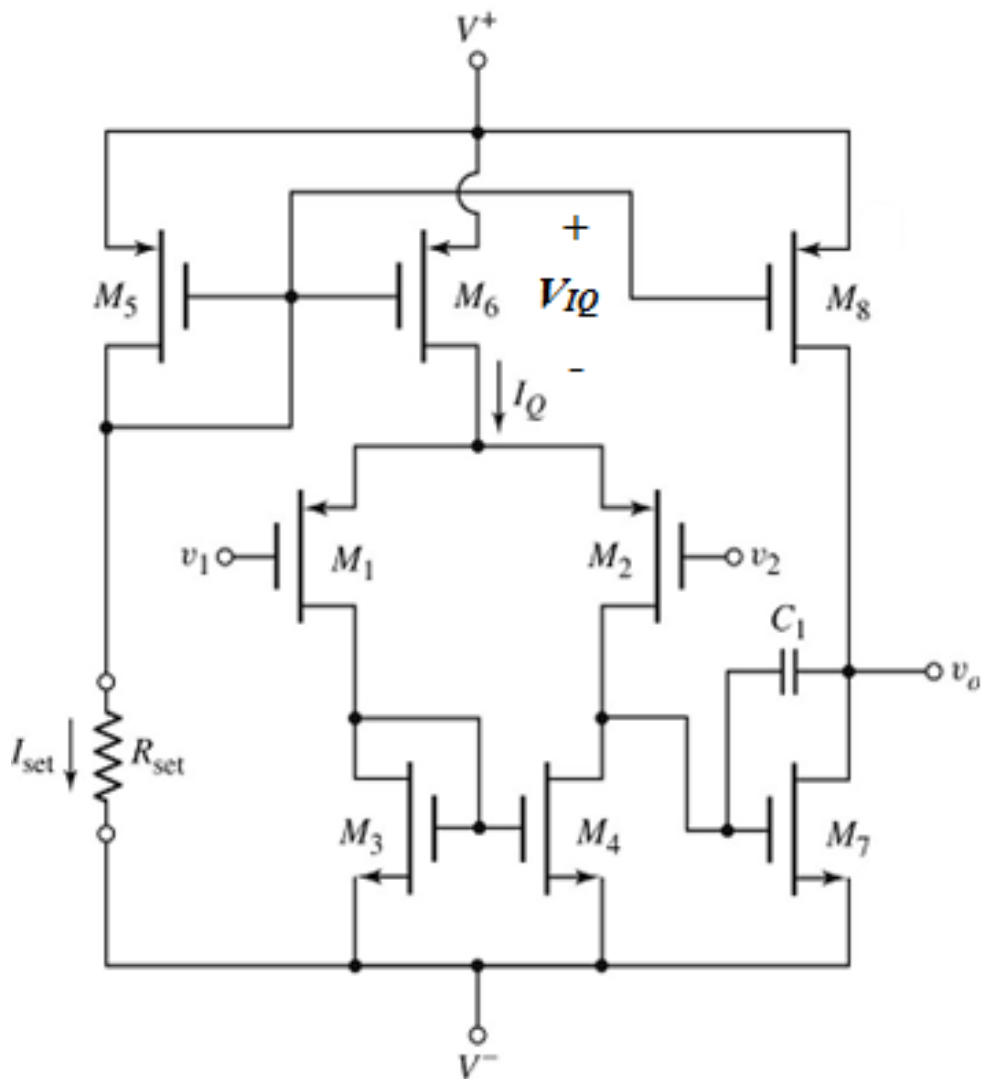
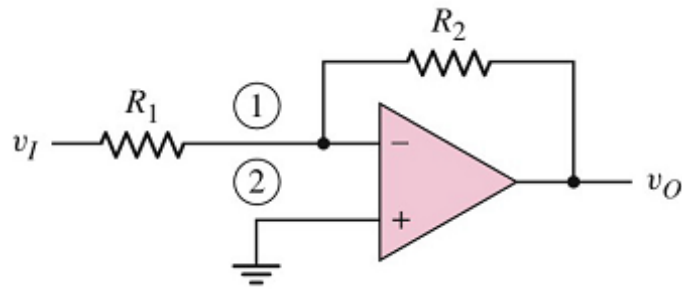


Figure 6

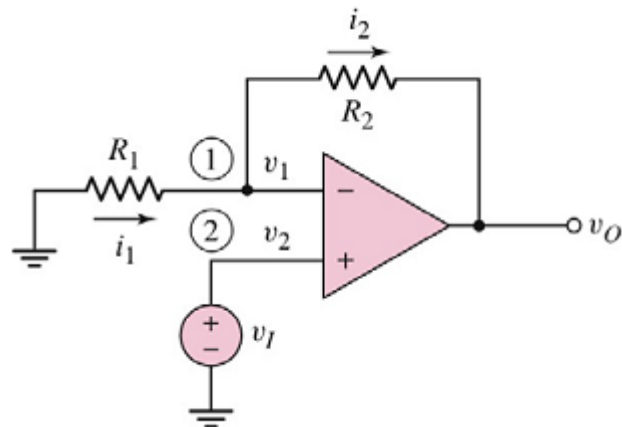
**Question 5 [20 marks]**

(a) Refer to **Figure 7** and **Figure 8** and answer the following questions.



**Figure 7**

- (i) **Identify** the ideal op-amp circuit in the **Figure 7** and **write the equation** that relates between its input voltage ( $v_I$ ) and output voltage ( $v_O$ ). **Modify** the circuit in the **Figure 7** to make an **inverting summing amplifier** with two (2) inputs  $v_{I1}$  and  $v_{I2}$  and **draw** the inverting summing amplifier circuit. **[3 marks]**



**Figure 8**

- (ii) **Identify** the ideal op-amp circuit in the **Figure 8** and **write the equation** that relates between its input voltage ( $v_I$ ) and output voltage ( $v_O$ ). **Calculate**  $v_O$  when  $v_I = 1.5 \text{ V}$ , and  $R_1 = R_2 = 25 \text{ k}\Omega$ . **[3 marks]**



- (b) Consider the ideal non-inverting op-amp circuit in **Figure 9**. Derive the expression for  $v_O$  as a function of  $v_{I1}$  and  $v_{I2}$ . Then, calculate  $v_O$  for  $v_{I1} = 0.2 \text{ V}$  and  $v_{I2} = 0.3 \text{ V}$ .

[6 marks]

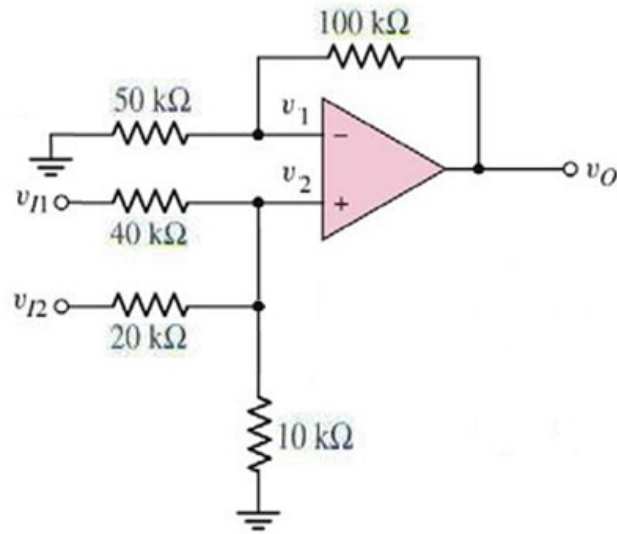


Figure 9

- (c) Assume the instrumentation amplifier in **Figure 10** has ideal op-amps. The circuit parameters are  $R_1 = 10 \text{ k}\Omega$ ,  $R_2 = 40 \text{ k}\Omega$ ,  $R_3 = 40 \text{ k}\Omega$ , and  $R_4 = 120 \text{ k}\Omega$ . Determine the current in  $R_1$  ( $i_1$ ) and voltages  $v_{O1}$ ,  $v_{O2}$ , and  $v_O$  when  $v_{I1} = -0.65 + 0.05 \sin \omega t \text{ (V)}$  and  $v_{I2} = -0.60 - 0.05 \sin \omega t \text{ (V)}$ .

[8 marks]

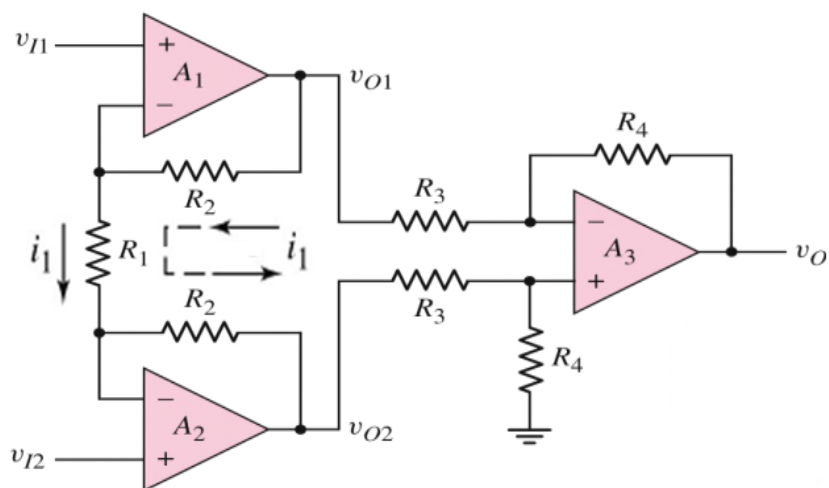


Figure 10

-END OF QUESTION PAPER-

**APPENDIX:**

**A) BASIC FORMULA FOR TRANSISTOR**

BJT

$$i_C = I_S e^{v_{BE}/V_T} \quad ; \text{NPN}$$

$$i_C = I_S e^{v_{EB}/V_T} \quad ; \text{PNP}$$

$$i_C = \beta i_B = \frac{\beta}{\beta + 1} i_E$$

$$i_E = i_B + i_C$$

; Small signal

$$\beta = g_m r_\pi$$

$$g_m = \frac{I_{CQ}}{V_T}$$

$$r_\pi = \frac{\beta V_T}{I_{CQ}}$$

$$r_o = \frac{V_A}{I_{CQ}}$$

$$V_T = 26 \text{ mV}$$

MOSFET

; N – MOSFET

$$v_{DS}(\text{sat}) = v_{GS} - V_{TN}$$

$$i_D = K_n [v_{GS} - V_{TN}]^2$$

$$K_n = \frac{\mu_n C_{ox} W}{2L} = \frac{k'_n}{2} \cdot \frac{W}{L}$$

; P – MOSFET

$$v_{SD}(\text{sat}) = v_{SG} + V_{TP}$$

$$i_D = K_p [v_{SG} + V_{TP}]^2$$

$$K_p = \frac{\mu_p C_{ox} W}{2L} = \frac{k'_p}{2} \cdot \frac{W}{L}$$

; Small signal

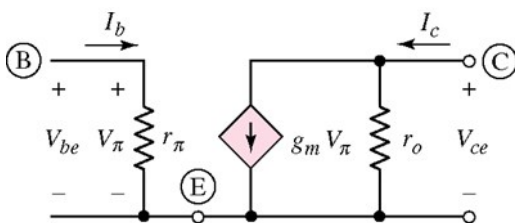
$$g_m = 2\sqrt{K_n I_{DQ}} \quad ; \text{N – MOSFET}$$

$$g_m = 2\sqrt{K_p I_{DQ}} \quad ; \text{P – MOSFET}$$

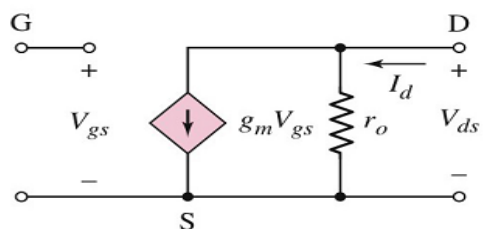
$$r_o \cong \frac{1}{\lambda I_{DQ}}$$

**B) HYBRID- $\pi$  EQUIVALENT CIRCUITS**

BJT



MOSFET



**C) QUADRATIC FORMULA**

$$Ax^2 + Bx + C = 0 \quad \rightarrow \quad x = \frac{-B \pm \sqrt{B^2 - 4AC}}{2A}$$